EVVOSEMI®
THINK CHANGE DO

ESD TVS MOS LDO Diode Sensor DC-DC

Product Specification

Domestic Part Number	IRLML2030
Overseas Part Number	IRLML2030
Equivalent Part Number	IRLML2030

Features

- $V_{DS\ (V)}$ = 30V
- $R_{DS(ON)}$ < 100mΩ (VGS = 10V)
- $R_{DS(ON)}$ < 154mΩ (VGS = 4.5V)

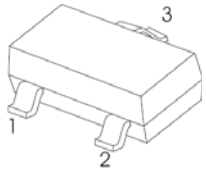
Application(s)

- Load/ System Switch

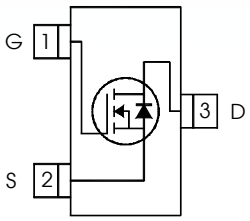
Benefits

- Multi-vendor compatibility
- Easier manufacturing RoHS
- Environmentally friendly
- Increased reliability

SOT－23



1. GATE
2. SOURCE
3. DRAIN



Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
V_{DS}	Drain-Source Voltage	30	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 10V	2.7	A
I_D @ T_A = 70°C	Continuous Drain Current, V_{GS} @ 10V	2.2	
I_{DM}	Pulsed Drain Current	11	
P_D @T_A = 25°C	Maximum Power Dissipation	1.3	W
P_D @T_A = 70°C	Maximum Power Dissipation	0.8	
	Linear Derating Factor	0.01	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient ③	——	100	°C/W
$R_{\theta JA}$	Junction-to-Ambient (t<10s) ④	——	99	

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

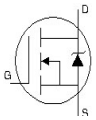
② Pulse width ≤ 400μs; duty cycle ≤ 2%.

③ Surface mounted on 1 in square Cu board

Electric Characteristics @ T_J = 25°C (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	V_{GS} = 0V, I_D = 250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.03	—	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	80	100	mΩ	V_{GS} = 10V, I_D = 2.7A ②
		—	123	154		V_{GS} = 4.5V, I_D = 2.2A ②
$V_{GS(th)}$	Gate Threshold Voltage	1.3	1.7	2.3	V	V_{DS} = V_{GS}, I_D = 25μA
I_{DSS}	Drain-to-Source Leakage Current	—	—	1	μA	V_{DS} =24V, V_{GS} = 0V
		—	—	150		V_{DS} = 24V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V_{GS} = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V_{GS} = -20V
R_G	Internal Gate Resistance	—	7.6	—	Ω	
gfs	Forward Transconductance	2.6	—	—	S	V_{DS} = 10V, I_D = 2.7A
Q_g	Total Gate Charge	—	1.0	—	nC	I_D = 2.7A
Q_{gs}	Gate-to-Source Charge	—	0.34	—		V_{DS} =15V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	0.34	—		V_{GS} = 4.5V ②
$t_{d(on)}$	Turn-On Delay Time	—	4.1	—	ns	V_{DD} =15V②
t_r	Rise Time	—	3.3	—		I_D = 1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	4.5	—		R_G = 6.8Ω
t_f	Fall Time	—	2.9	—		V_{GS} = 4.5V
C_{iss}	Input Capacitance	—	110	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	29	—		V_{DS} = 15V
C_{rss}	Reverse Transfer Capacitance	—	12	—		f = 1.0MHz

Source - Drain Ratings and Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	1.6	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	11		
V_{SD}	Diode Forward Voltage	—	—	1.0	V	T_J = 25°C, I_S = 2.7A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	—	9.0	14	ns	T_J = 25°C, V_R = 15V, I_F=2.7A
Q_{rr}	Reverse Recovery Charge	—	0.3	0.4	nC	di/dt = 100A/μs ②

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

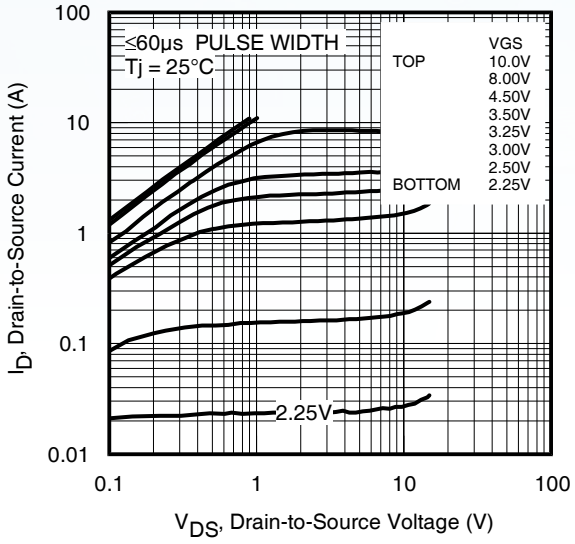


Fig 1. Typical Output Characteristics

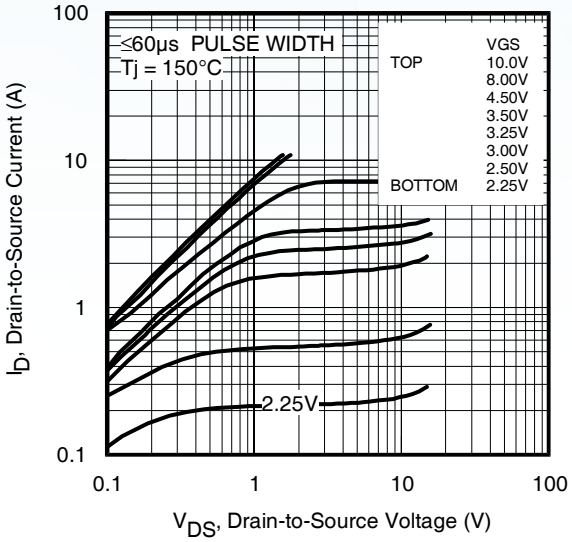


Fig 2. Typical Output Characteristics

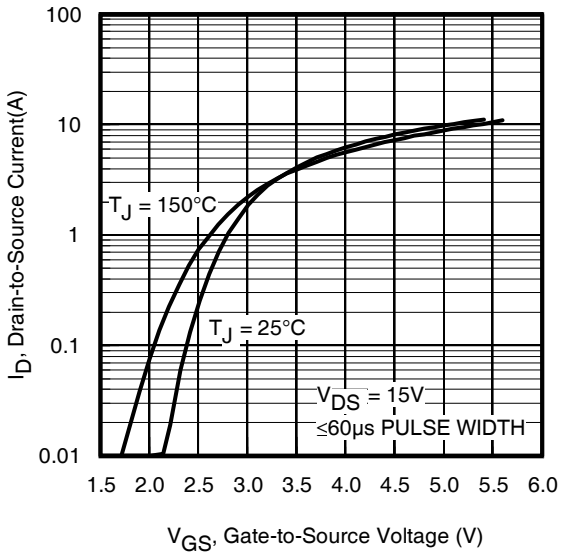


Fig 3. Typical Transfer Characteristics

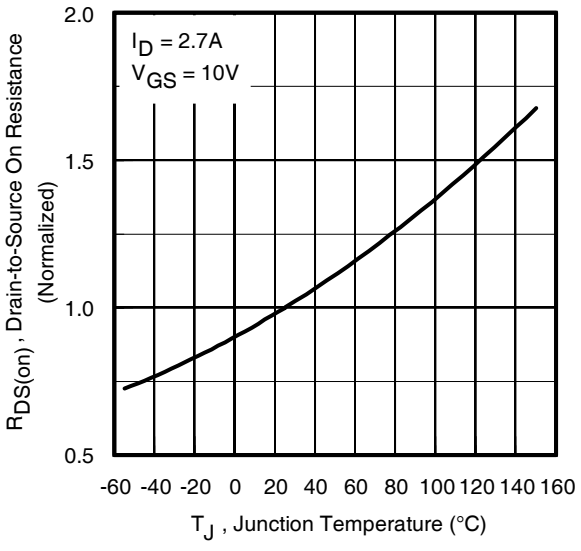


Fig 4. Normalized On-Resistance Vs. Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

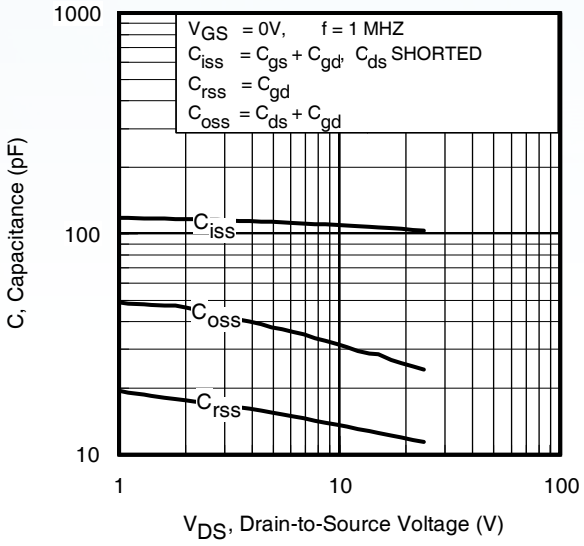


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

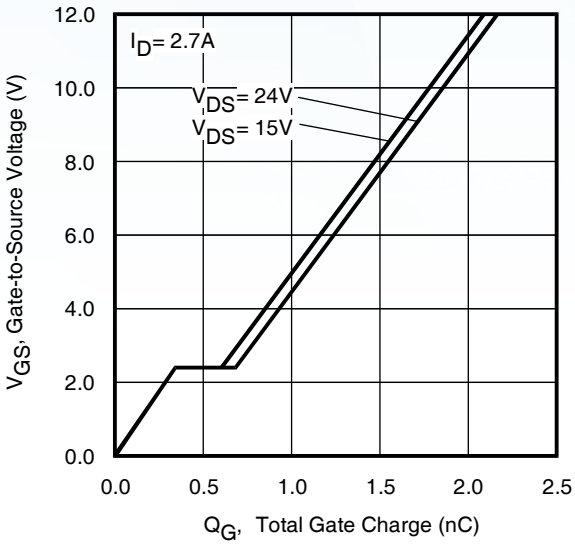


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

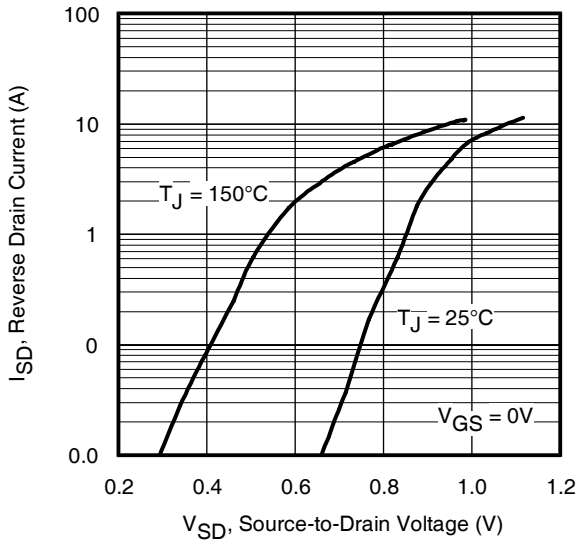


Fig 7. Typical Source-Drain Diode Forward Voltage

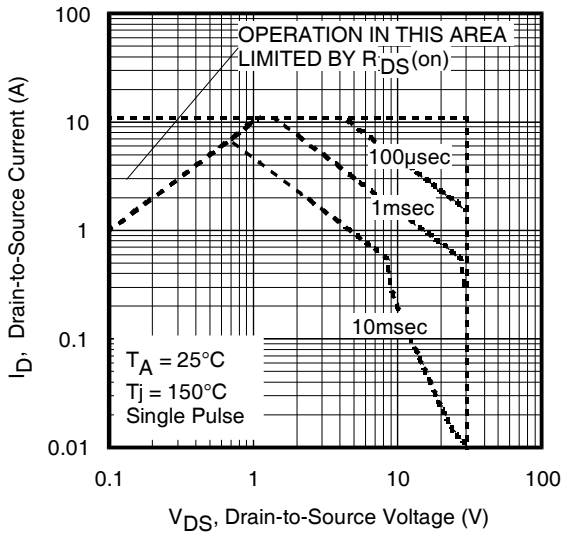


Fig 8. Maximum Safe Operating Area

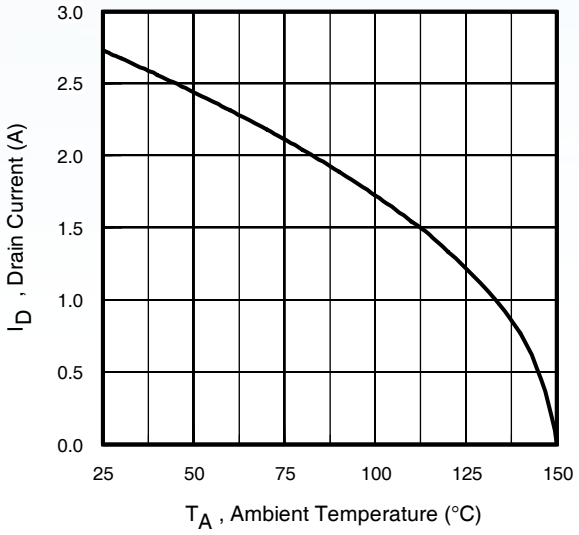


Fig 9. Maximum Drain Current Vs. Ambient Temperature

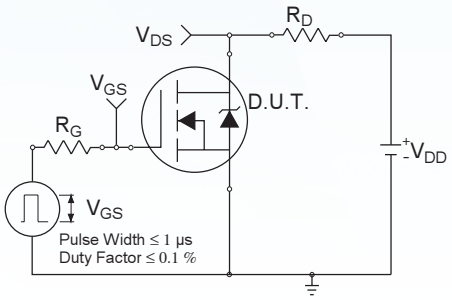


Fig 10a. Switching Time Test Circuit

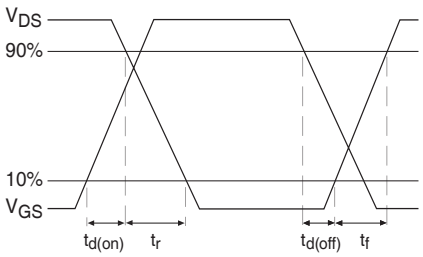


Fig 10b. Switching Time Waveforms

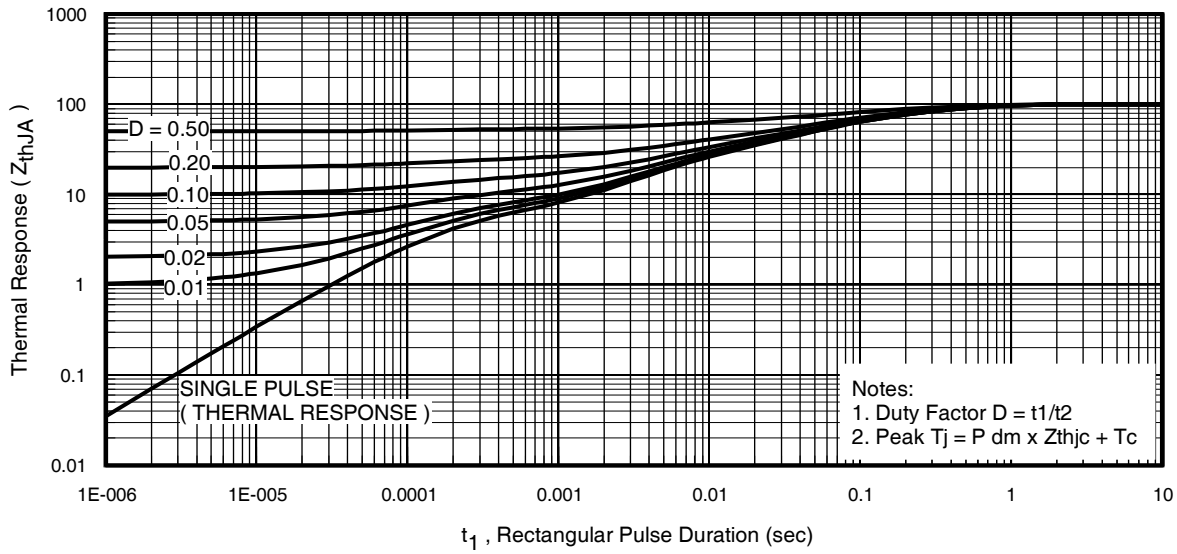


Fig 11. Typical Effective Transient Thermal Impedance, Junction-to-Ambient

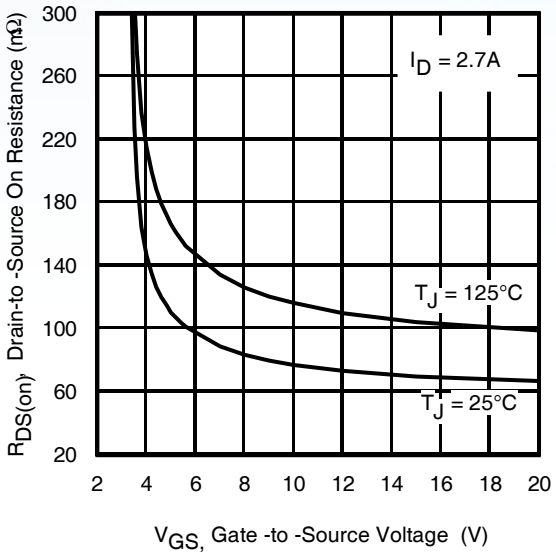


Fig 12. Typical On-Resistance Vs. Gate Voltage

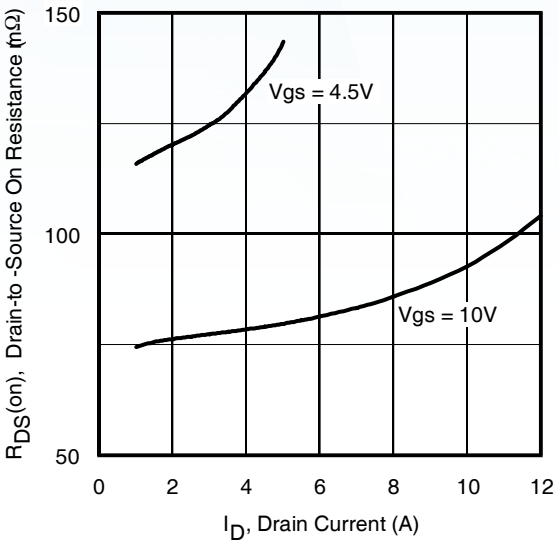


Fig 13. Typical On-Resistance Vs. Drain Current

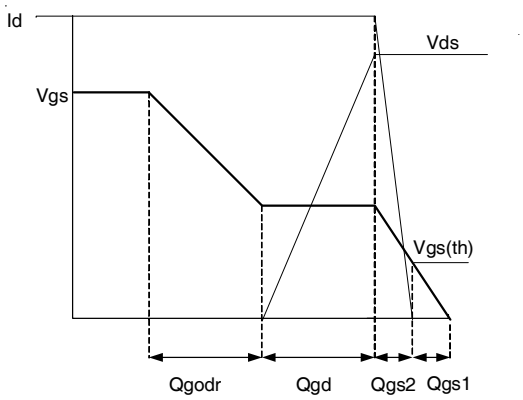


Fig 14a. Basic Gate Charge Waveform

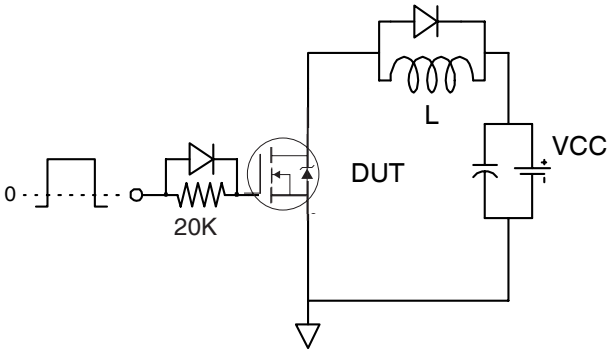


Fig 14b. Gate Charge Test Circuit

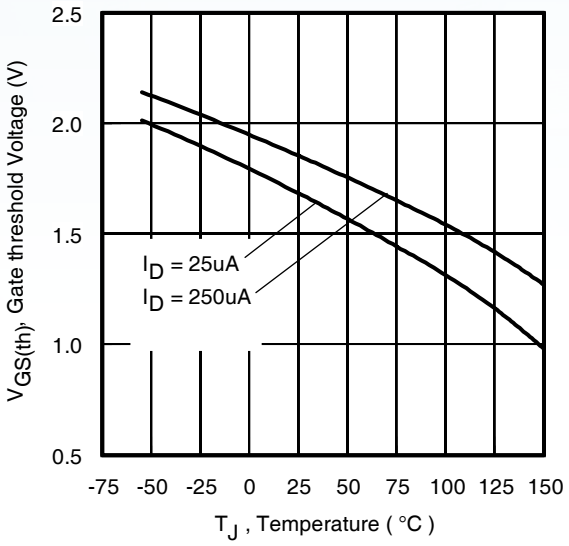


Fig 15. Typical Threshold Voltage Vs. Junction Temperature

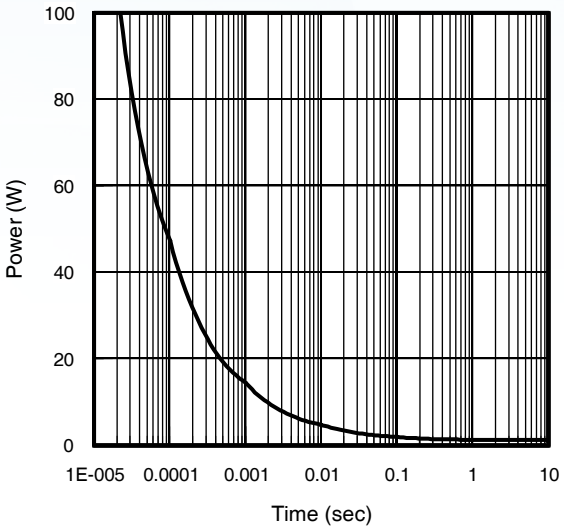
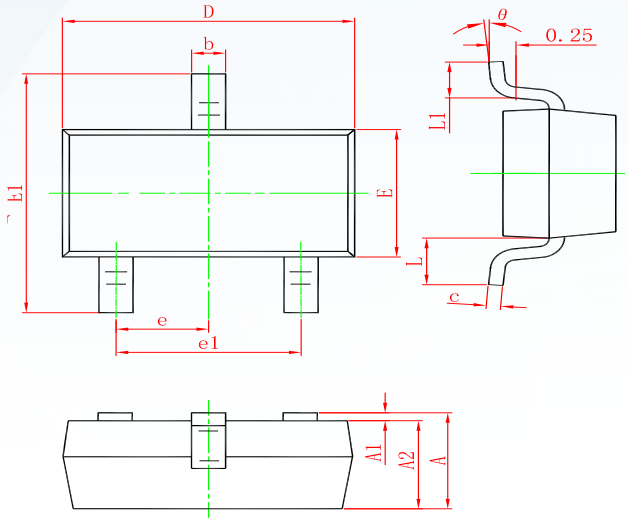


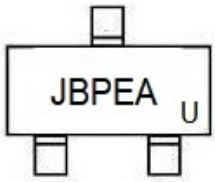
Fig 16. Typical Power Vs. Time

SOT-23 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Marking



Ordering information

Order code	Package	Baseqty	Deliverymode
IRLML2030	SOT-23	3000	Tape and reel

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